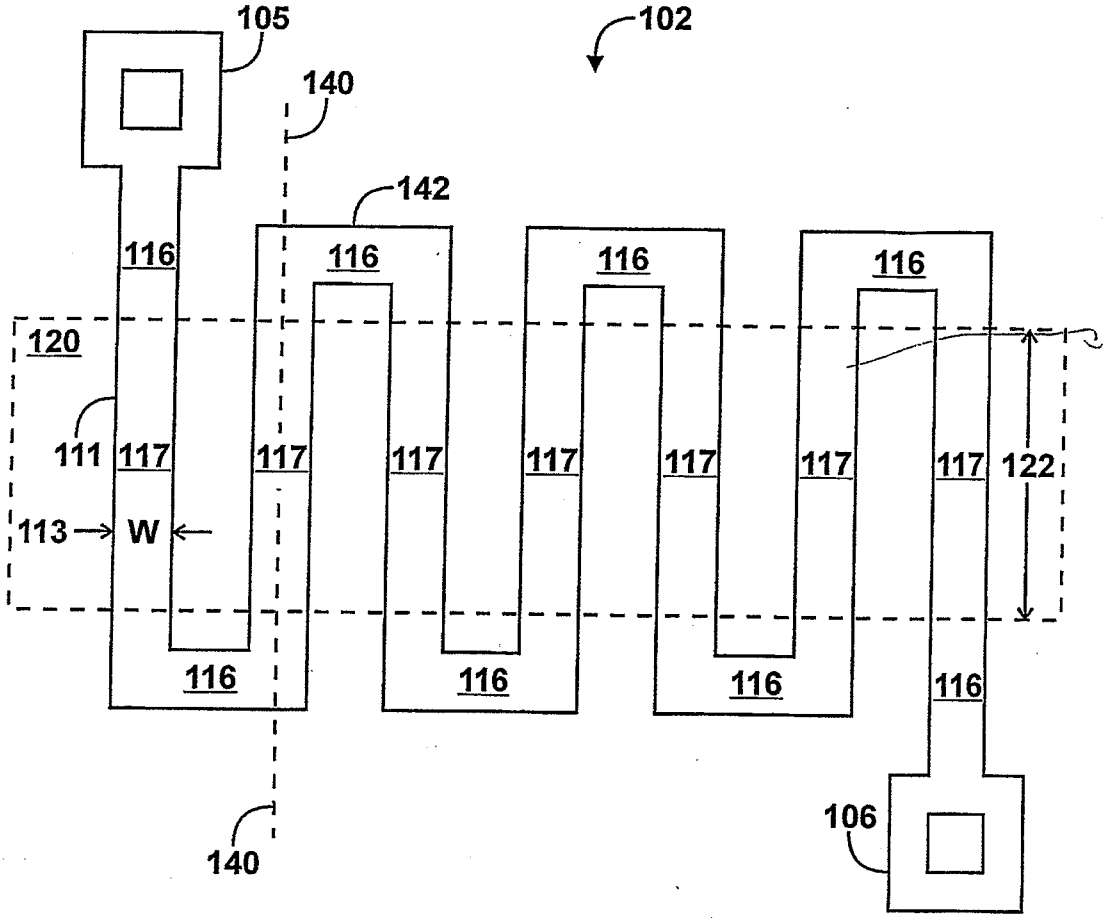

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FIG. 1

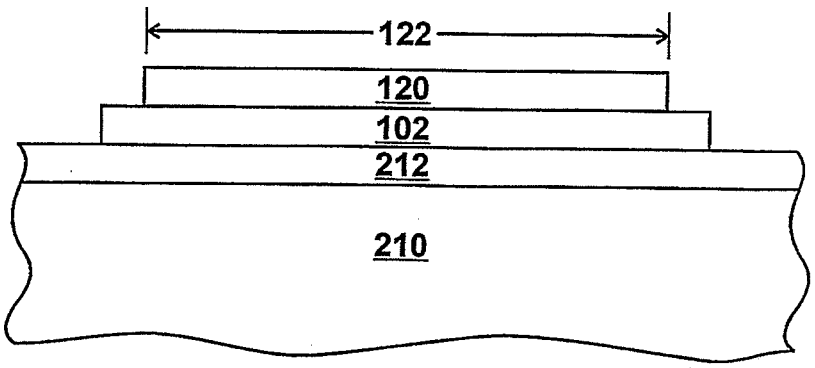

122
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FIG. 2

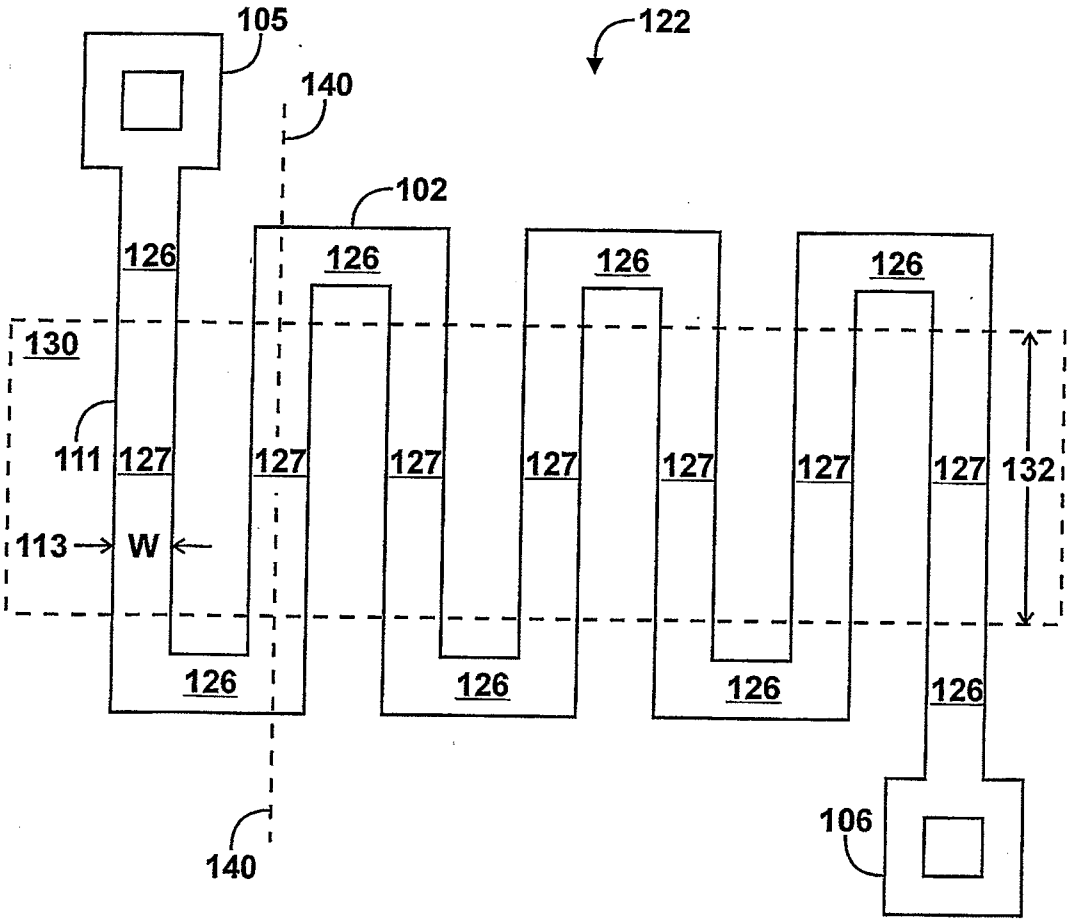

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FIG. 3

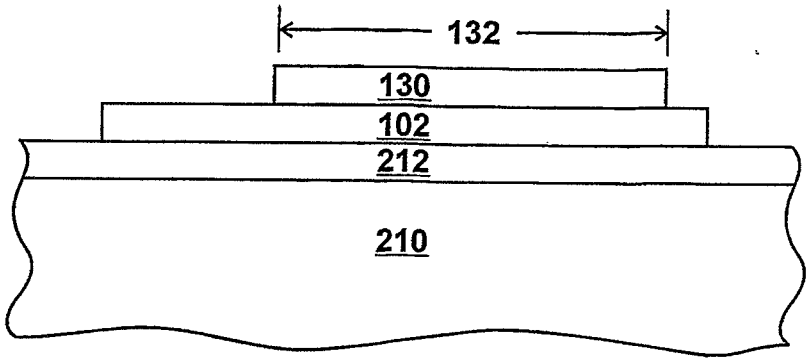



FIG. 4

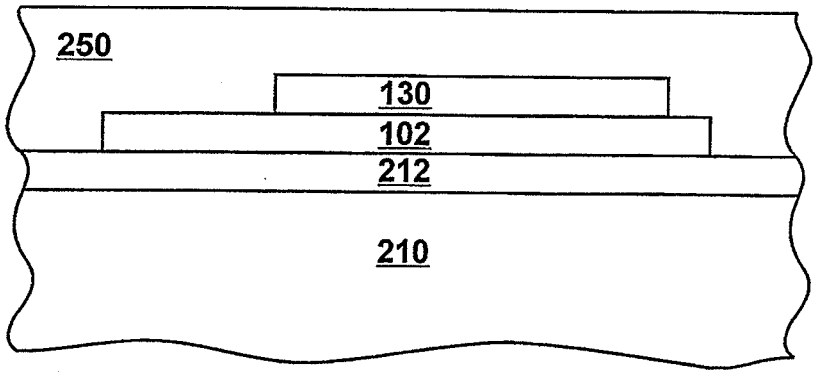



FIG. 5

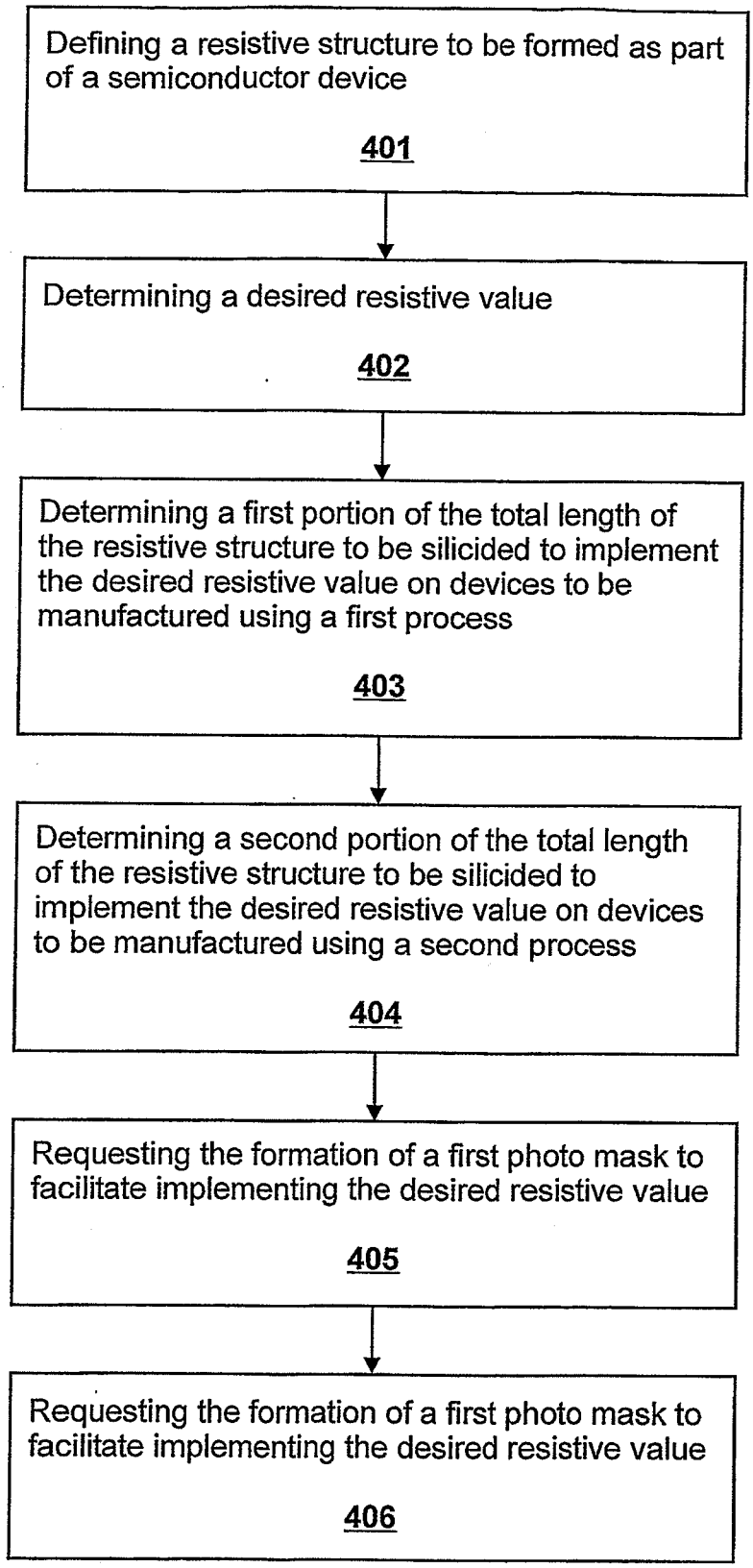

Defining a resistive structure to be formed as part of a semiconductor device
401
Determining a desired resistive value
402
Determining a first portion of the total length of the resistive structure to be silicided to implement the desired resistive value on devices to be manufactured using a first process
403
Determining a second portion of the total length of the resistive structure to be silicided to implement the desired resistive value on devices to be manufactured using a second process
404
Requesting the formation of a first photo mask to facilitate implementing the desired resistive value
405
Requesting the formation of a first photo mask to facilitate implementing the desired resistive value
406

FIG. 6

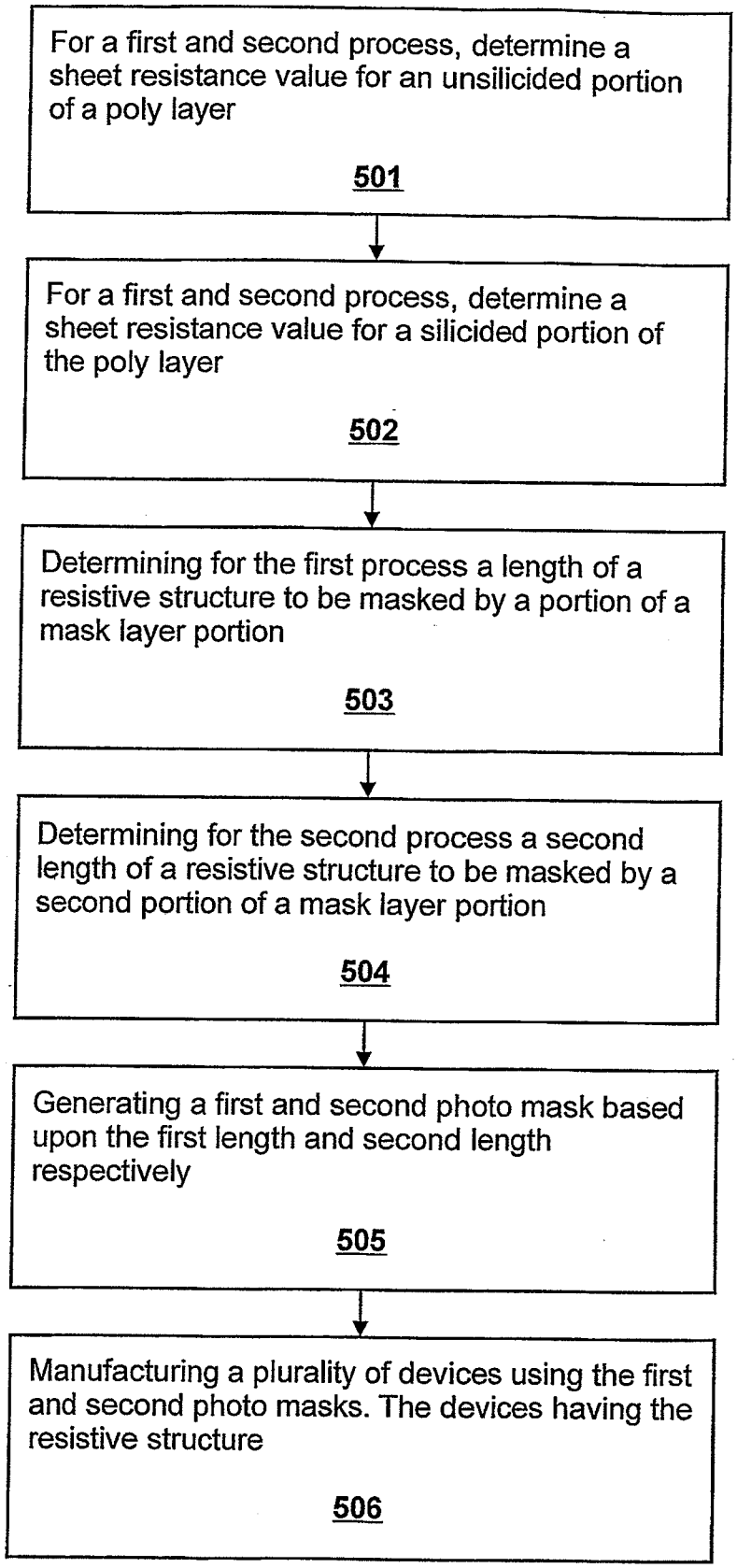

For a first and second process, determine a sheet resistance value for an unsilicided portion of a poly layer
501
For a first and second process, determine a sheet resistance value for a silicided portion of the poly layer
502
Determining for the first process a length of a resistive structure to be masked by a portion of a mask layer portion
503
Determining for the second process a second length of a resistive structure to be masked by a second portion of a mask layer portion
504
Generating a first and second photo mask based upon the first length and second length respectively
505
Manufacturing a plurality of devices using the first and second photo masks. The devices having the resistive structure
506

FIG. 7

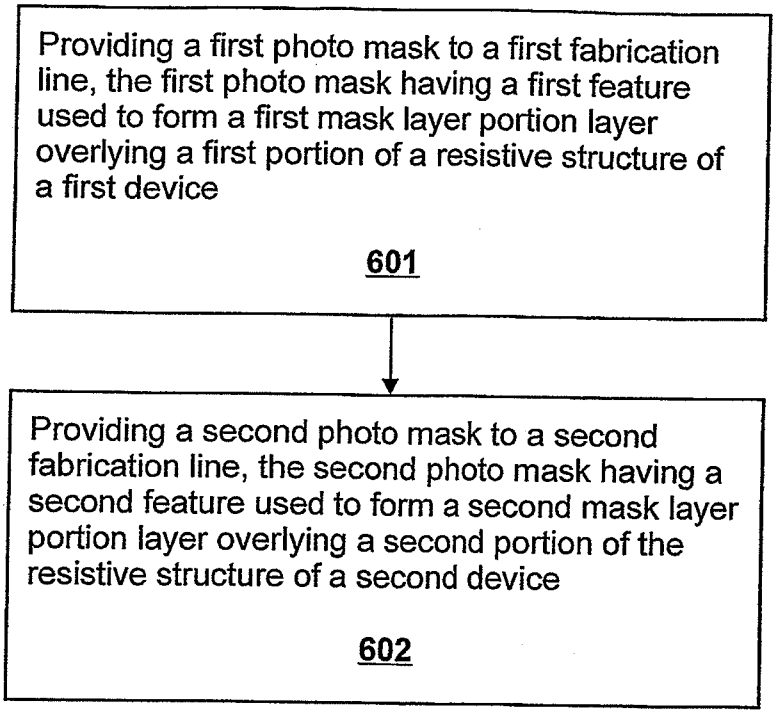

Providing a first photo mask to a first fabrication line, the first photo mask having a first feature used to form a first mask layer portion layer overlying a first portion of a resistive structure of a first device
601
Providing a second photo mask to a second fabrication line, the second photo mask having a second feature used to form a second mask layer portion layer overlying a second portion of the resistive structure of a second device
602

FIG. 8